



A Product Line of Diodes Incorporated



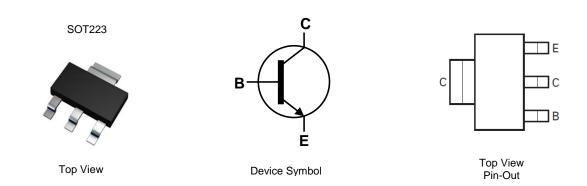
30V NPN MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > 30V
- I_C = 1A High Continuous Current
- I_{CM} = 4A Peak Pulse Current
- Low Saturation Voltage
- Complementary PNP Type: FZT589
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT223
- Case material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (€3)
- Weight: 0.112 grams (Approximate)



Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT489TA	AEC-Q101	FZT489	7	12	1,000
FZT489QTA	Automotive	FZT489	7	12	1,000

EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

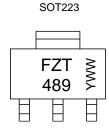
Alalogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
<1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Notes:



FZT 489 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)





Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	1	A
Base Current	IB	200	mA
Peak Pulse Current	I _{CM}	4	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 6)		3.0		
Power Dissipation	(Note 7)	D-	2.0	W	
	(Note 8)	PD	1.6	vv	
	(Note 9)		1.2		
	(Note 6)		41.7		
Thermal Resistance, Junction to Ambient	(Note 7)		62.5		
merma Resistance, Junction to Ambient	(Note 8)	R _{θJA}	78.1	°C/W	
	(Note 9)		104		
Thermal Resistance Junction to Lead (Note 10)		R _{θJL}	19.4		
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C		

ESD Ratings (Note 11)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

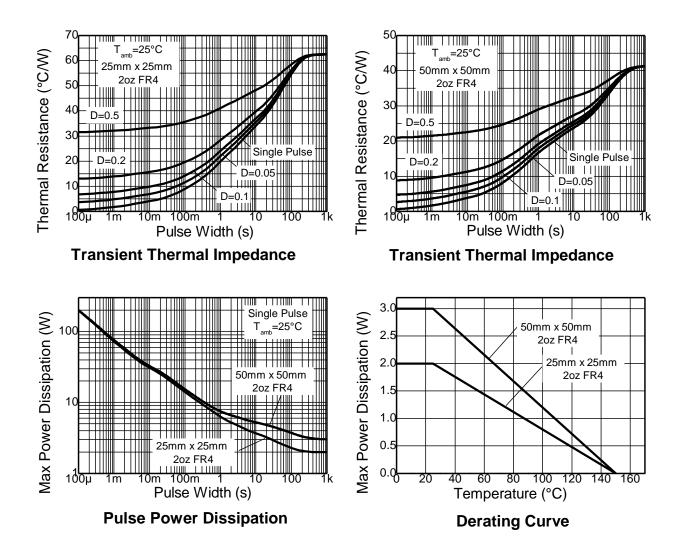
6. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under Notes: still air conditions whilst operating in a steady-state. 7. Same as Note 6, except the device is mounted on 25mm x 25mm 2oz copper.

Same as Note 6, except the device is mounted on 25mm x 25mm 102 copper.
Same as Note 6, except the device is mounted on 25mm x 25mm 10z copper.
Same as Note 6, except the device is mounted on minimum recommended pad layout.
Thermal resistance from junction to solder-point (at the end of the collector lead).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.





Thermal Characteristics and Derating Characteristics







Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

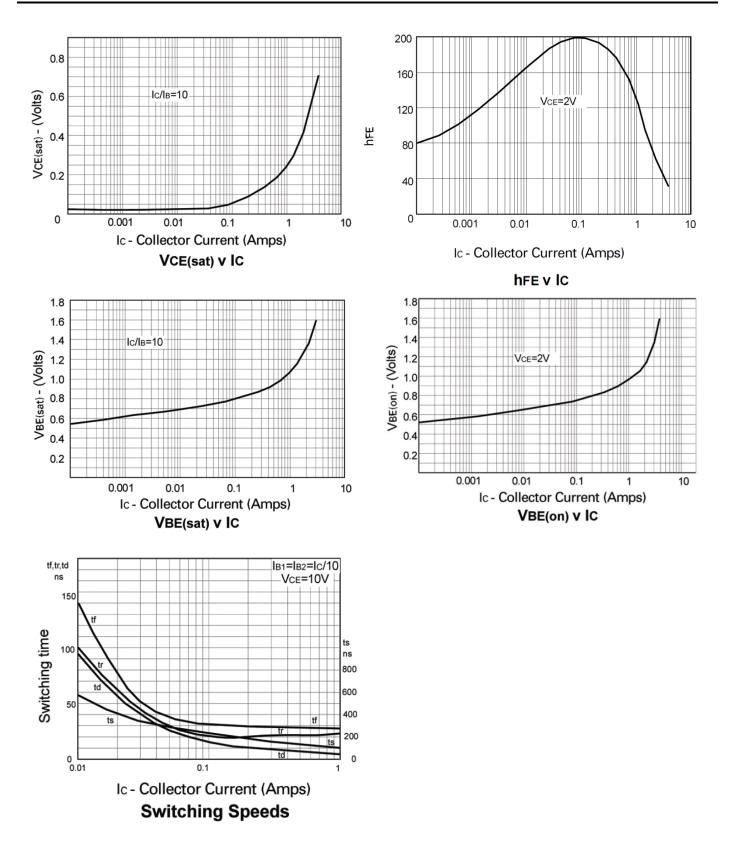
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	50	_	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 12)	BV _{CEO}	30	-	-	V	$I_{C} = 10 \text{mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	_	_	V	I _E = 100μA
Collector Cut-Off Current	I _{CBO}	-	-	100	nA	$V_{CB} = 30V$
Collector Cut-Off Current	I _{CES}	-	-	100	nA	V _{CE} = 30V
Emitter Cut-Off Current	I _{EBO}	-	-	100	nA	$V_{EB} = 4V$
Collector-Emitter Saturation Voltage (Note 12)	V _{CE(sat)}	-	-	0.3 0.6	V	$I_{C} = 1A, I_{B} = 100mA$ $I_{C} = 2A, I_{B} = 200mA$
Base-Emitter Saturation Voltage (Note 12)	V _{BE(sat)}	-	-	1.1	V	$I_{C} = 1A, I_{B} = 100mA$
Base-Emitter Turn-On Voltage (Note 12)	V _{BE(on)}	-	-	1.0	V	$I_{C} = 1A, V_{CE} = 2V$
DC Current Gain (Note 12)	h _{FE}	100 100 60 20	- - -	 300 	_	$\begin{split} I_{C} &= 1 \text{mA}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 1 \text{A}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 2 \text{A}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 4 \text{A}, \ V_{CE} = 2 \text{V} \end{split}$
Current Gain-Bandwidth Product	fT	150	-	-	MHz	$V_{CE} = 10V, I_C = 50mA$ f = 100MHz
Output Capacitance	C _{obo}	-	-	10	pF	$V_{CB} = 10V, f = 1MHz$

12. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%. Note:





Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

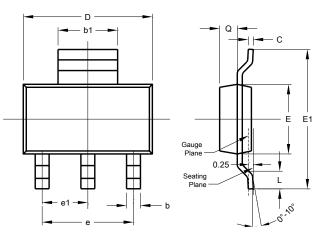


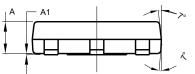




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

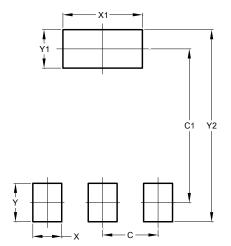




SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
ш	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00





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